



(12) **United States Design Patent** (10) **Patent No.:** **US D901,406 S**
Kagaya et al. (45) **Date of Patent:** **** Nov. 10, 2020**

(54) **INNER TUBE OF REACTOR FOR SEMICONDUCTOR FABRICATION**

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(51) **LOC (12) Cl.** **13-03**

(52) **U.S. Cl.**
USPC **D13/182**

(58) **Field of Classification Search**
USPC D13/182
CPC H01L 21/67098; H01L 21/67103; H01L 21/67109; H01L 21/67115; C23C 16/455; C23C 16/45502; C23C 16/45504; C23C 16/45506; C23C 16/45508; C23C 16/4551; C23C 16/4586; C23C 16/4587; C23C 16/46; C23C 16/463; C23C 16/466
See application file for complete search history.

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(57) **CLAIM**

The ornamental design for an inner tube of reactor for semiconductor fabrication, as shown and described.

DESCRIPTION

FIG. 1 is a front, top and right side perspective view of an inner tube of reactor for semiconductor fabrication showing our new design;

FIG. 2 is a front elevational view thereof;

FIG. 3 is a rear elevational view thereof;

FIG. 4 is a right side elevational view thereof;

FIG. 5 is a left side elevational view thereof;

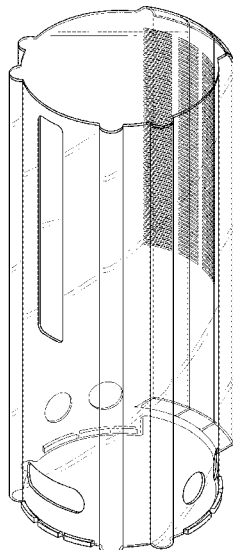
FIG. 6 is a top plan view thereof;

FIG. 7 is a bottom plan view thereof;

FIG. 8 is a cross sectional view taken along line 8-8 in FIG. 2; and,

FIG. 9 is a cross sectional view taken along line 9-9 in FIG. 8.

1 Claim, 8 Drawing Sheets



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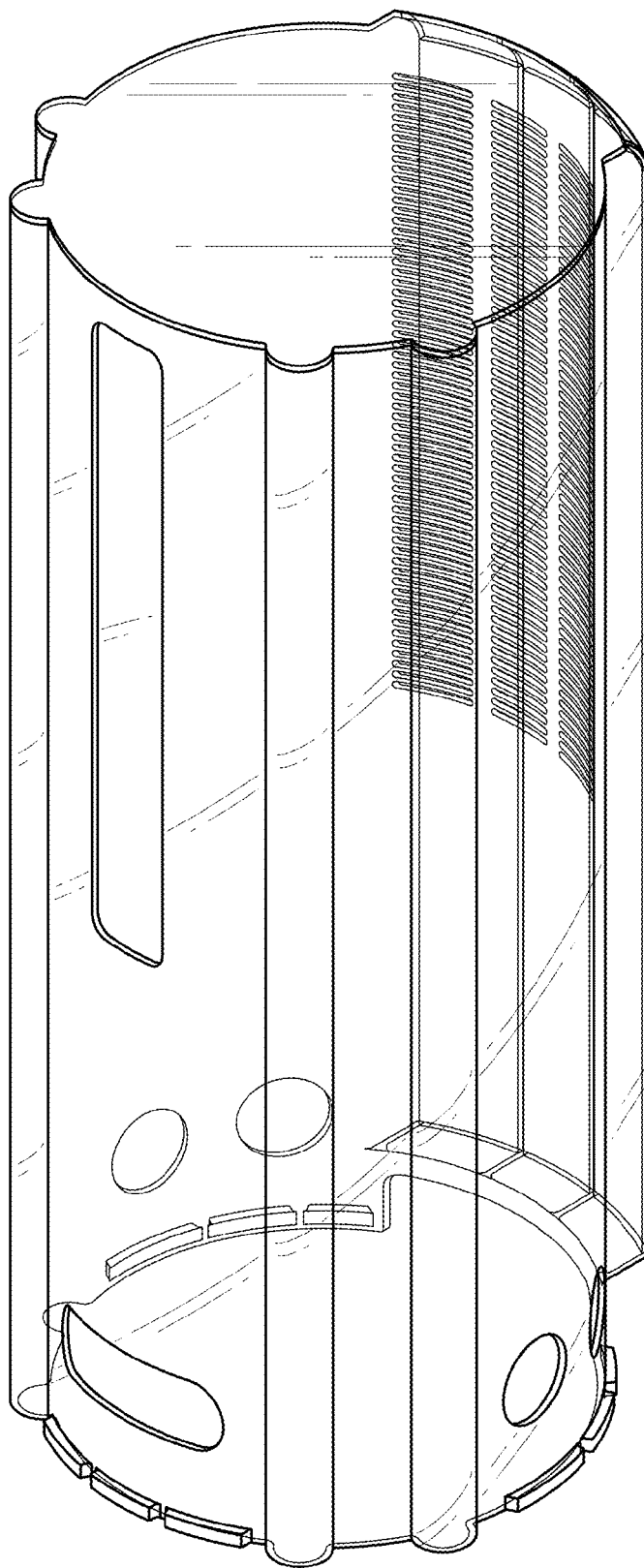


FIG. 1

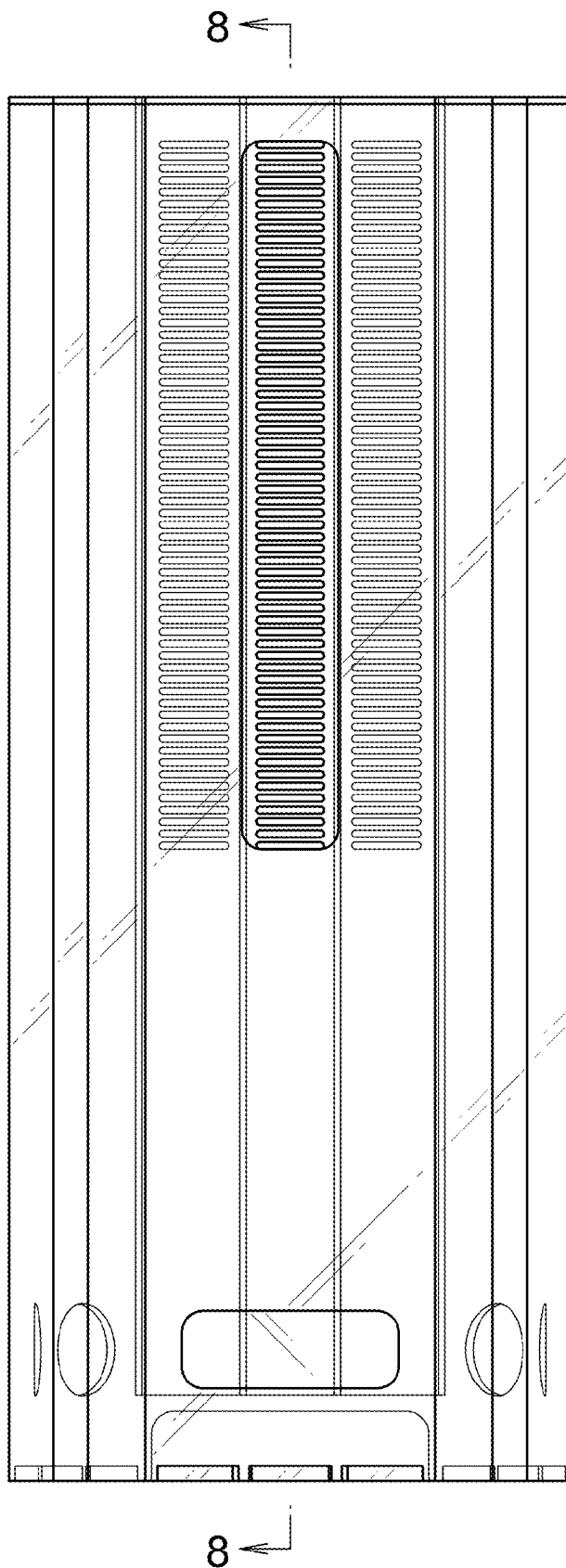


FIG. 2

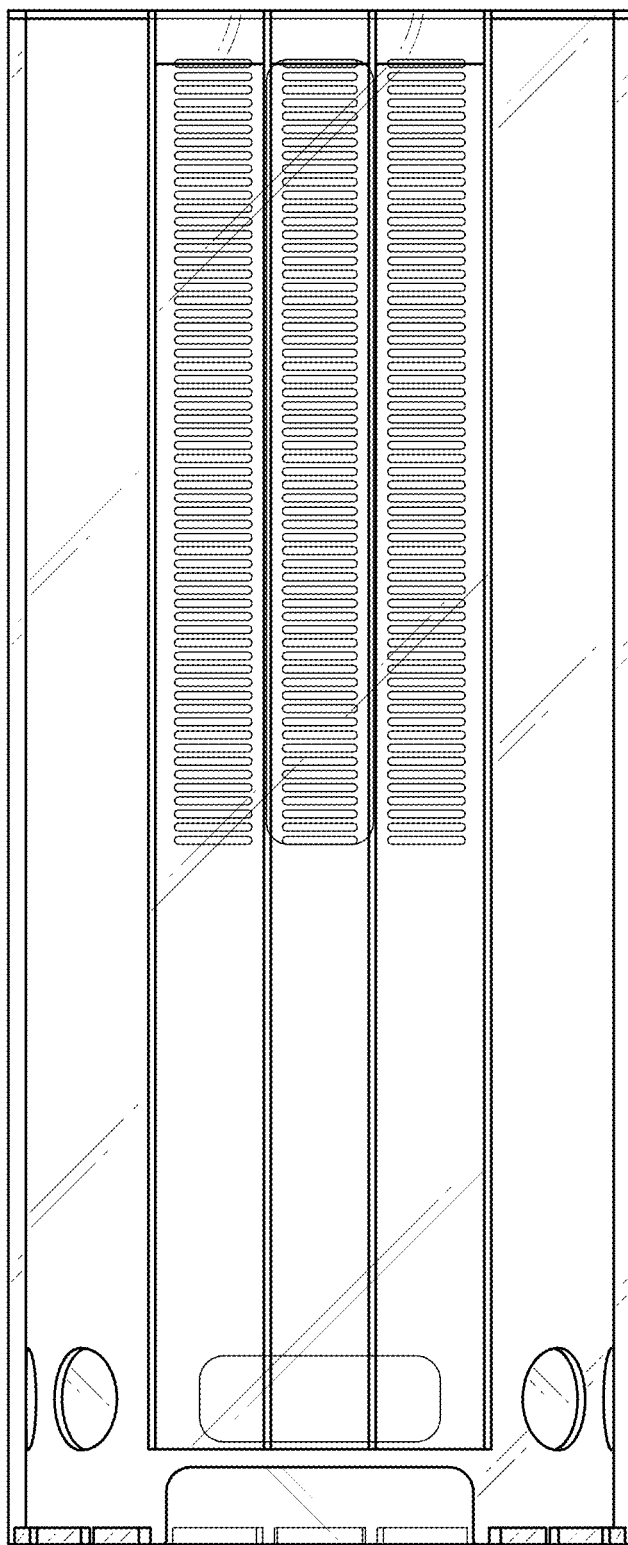


FIG. 3

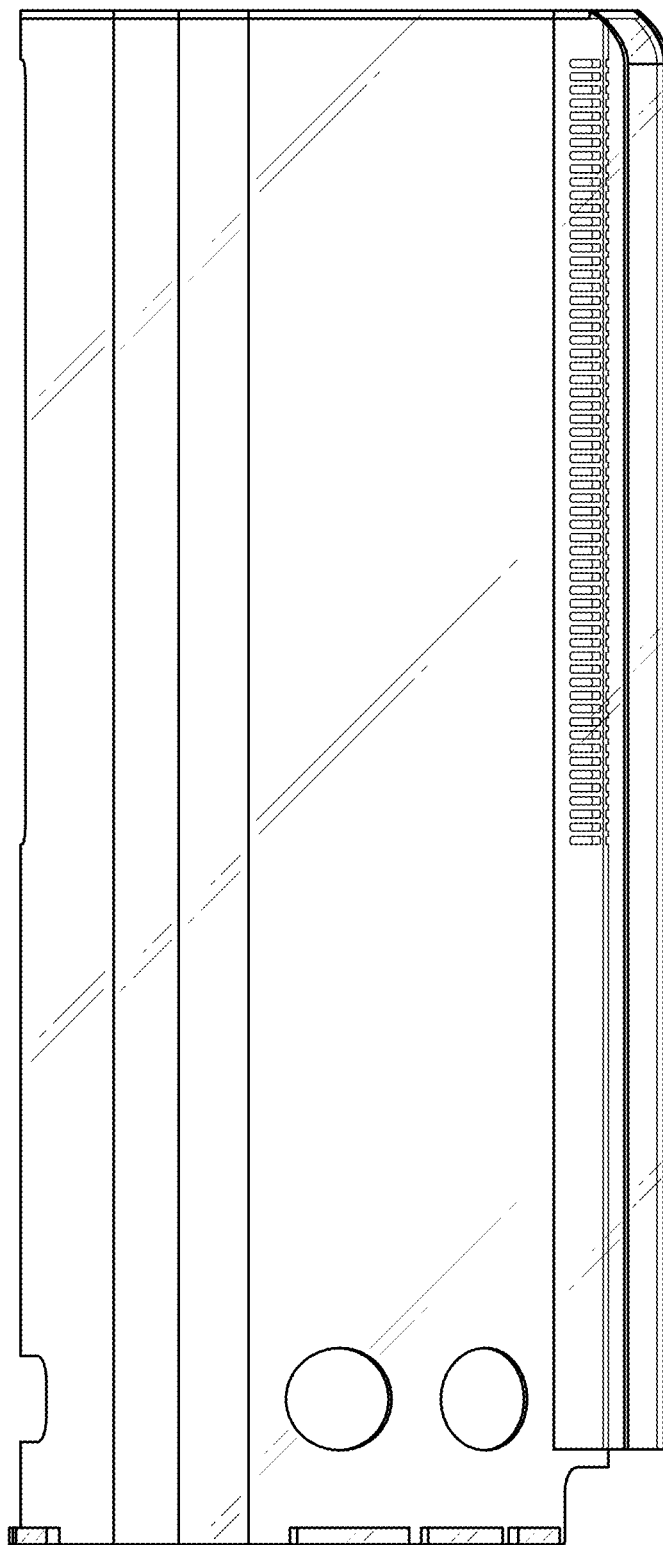


FIG. 4

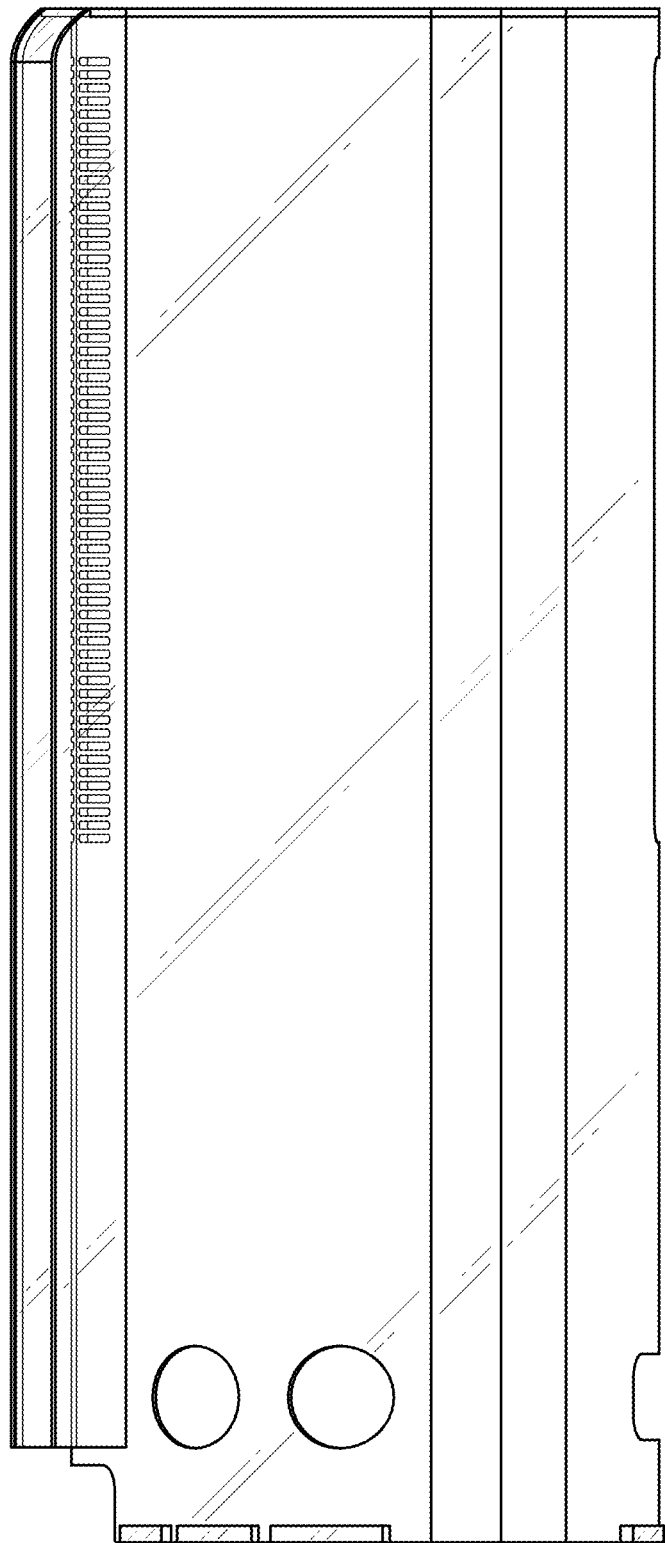


FIG. 5

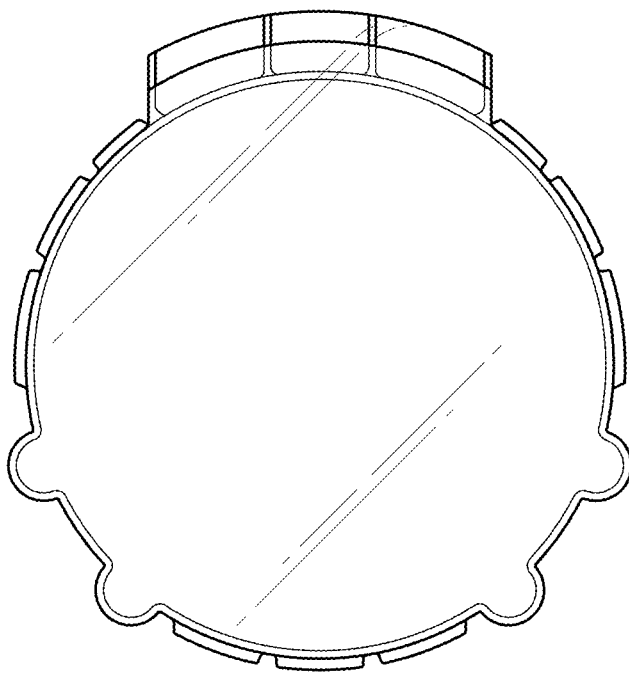


FIG. 6

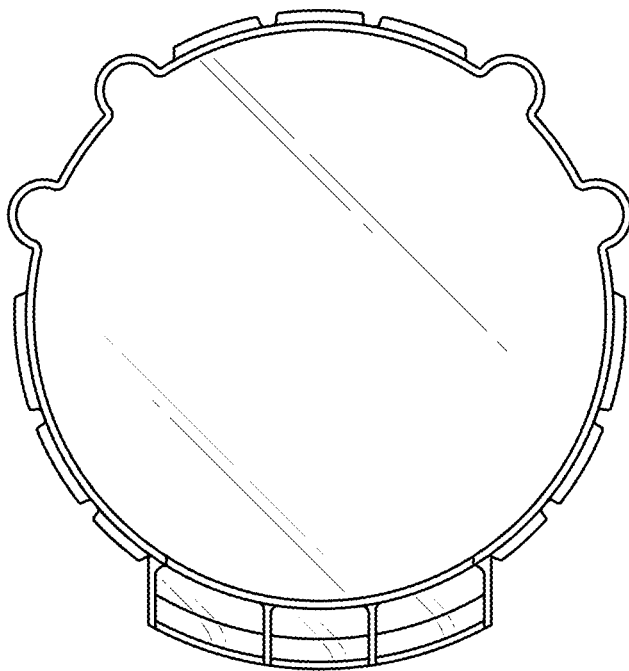


FIG. 7

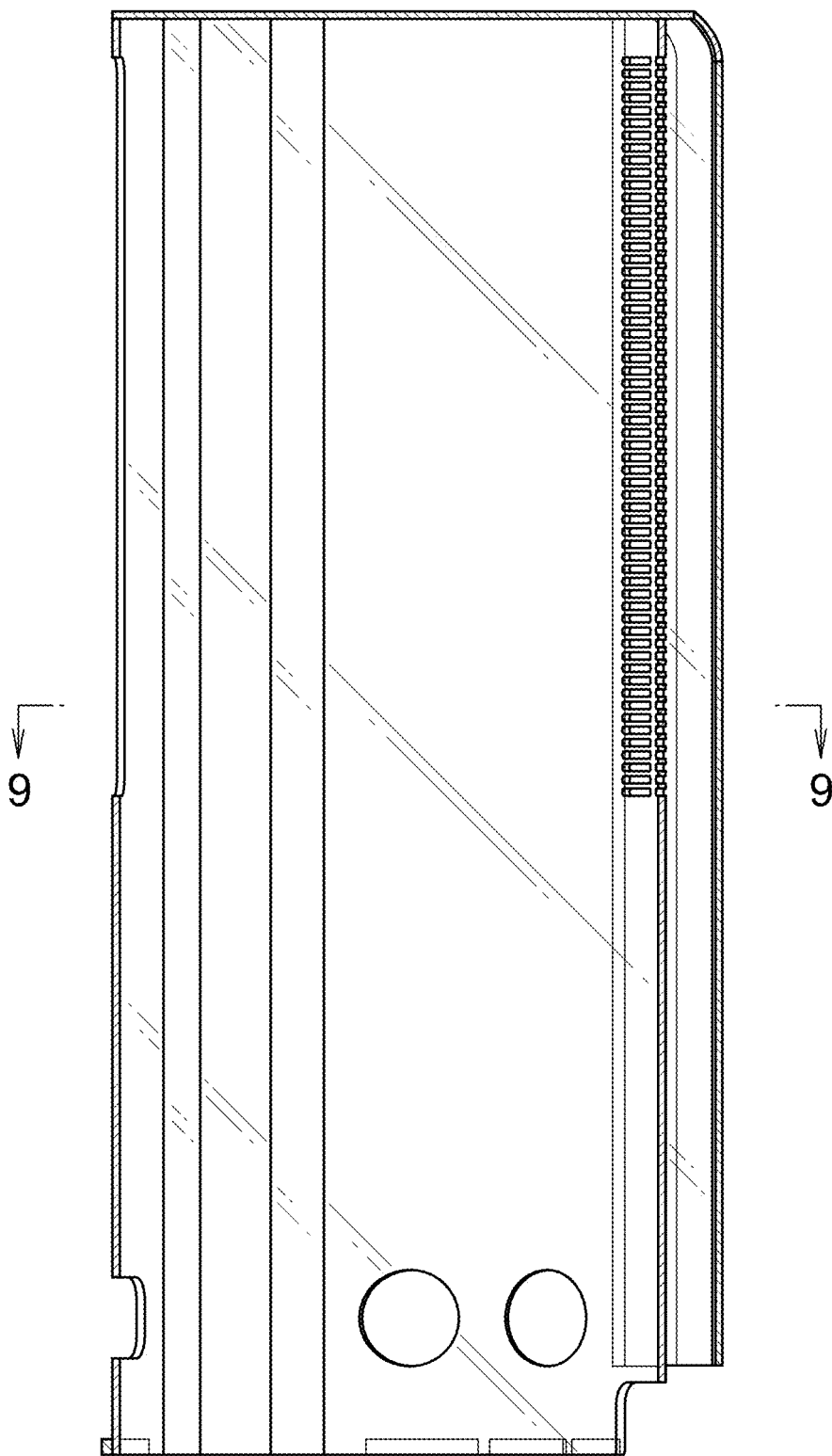


FIG. 8

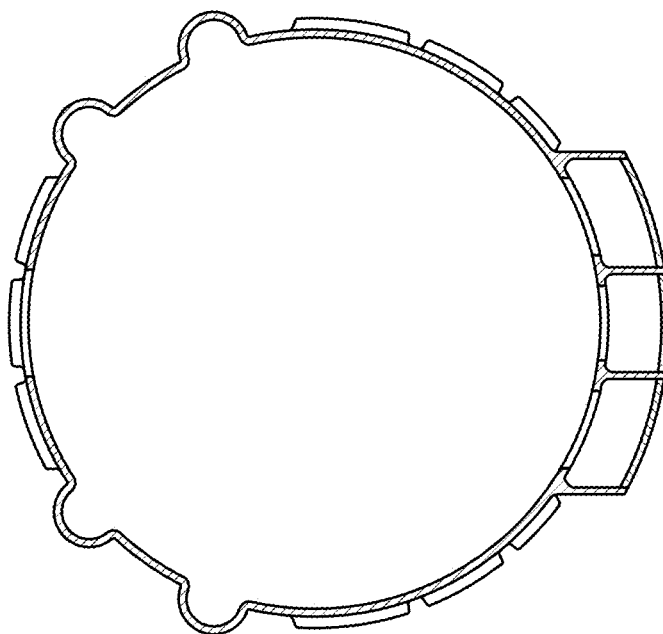


FIG. 9